

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:

5 a thin film transistor provided between an element to be driven which operates based on supplied power and a power supply line for supplying power to said element to be driven, for controlling the power supplied to said element to be driven; wherein

10 the thin film transistor and corresponding element to be driven are electrically connected to each other by a wiring layer; and

15 the contact position between the wiring layer and the thin film transistor is placed to be distant from the contact position between the wiring layer and said element to be driven.

2. A semiconductor device according to claim 1, wherein

20 said element to be driven is an emissive element which includes an emissive element layer between a first electrode and a second electrode;

25 a contact hole is formed on an insulation layer which is formed above said wiring layer, said wiring layer being connected through the contact hole to said first electrode of said emissive element which is formed on top of said insulation layer and covering said contact hole;

at least the contact hole region of said first electrode is covered by a flattening layer; and

said emissive element layer is formed above said first electrode and said flattening layer.

3. A semiconductor device comprising:

a thin film transistor for controlling power supplied to an element to be driven which operates based on the supplied power and which includes an emissive element layer between a first electrode and a second electrode, said thin film transistor provided
5 between said element to be driven and a power supply line for supplying power to said element to be driven; wherein

~~the thin film transistor and corresponding element to be~~
driven are directly or indirectly and electrically connected to each other at a contact hole formed on an insulation layer for separating said thin film transistor which is formed at a lower layer and said element to be driven;

at least the contact hole region of said first electrode is covered by a flattening layer; and

said emissive element layer is formed above said first electrode and said flattening layer.

4. A semiconductor device according to claim 1, wherein said element to be driven is an organic electroluminescence element which uses an organic compound in an emissive layer.